

# EMH15 / IMH15A

NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

Parameter	Tr1 and Tr2
V <sub>CEO</sub>	50V
I <sub>C(MAX.)</sub>	100mA
R <sub>1</sub>	47kΩ

#### Features

- 1) Built-In Biasing Resistors.
- 2) Two DTC144T chips in one package.
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

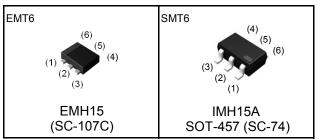
#### Application

Inverter circuit, Interface circuit, Driver circuit

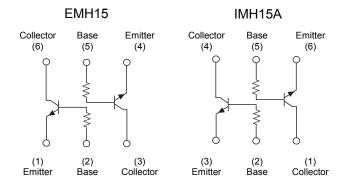
#### Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMH15	EMT6	1616	T2R	180	8	8,000	H15
IMH15A	SMT6	2928	T110	180	8	3,000	H15

#### Outline



#### Inner circuit



#### ●Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter		Symbol	Values	Unit
Collector-base voltage		V <sub>CBO</sub>	50	V
Collector-emitter voltage		V <sub>CEO</sub>	50	V
Emitter-base voltage		V <sub>EBO</sub>	5	V
Collector current		۲ ا <sub>C(MAX.)</sub> *1	100	mA
Collector Power dissipation	EMH15	– P <sub>D</sub> <sup>*2</sup>	150 (Total) <sup>*3</sup>	mW
IMH15A			300 (Total) <sup>*4</sup>	mW
Junction temperature		Tj	150	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +150	°C

#### •Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	$BV_{CBO}$	I <sub>C</sub> = 50μA	50	-	-	V
Collector-emitter breakdown voltage	$BV_{CEO}$	I <sub>C</sub> = 1mA	50	-	-	V
Emitter-base breakdown voltage	$BV_{EBO}$	I <sub>E</sub> = 50μA	5	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 50V	-	-	0.5	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	-	-	0.5	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> / I <sub>B</sub> = 5mA / 0.5mA	-	-	0.3	V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V , I <sub>C</sub> = 1mA	100	250	600	-
Input resistance	R <sub>1</sub>	-	32.9	47	61.1	kΩ
Transition frequency	f <sub>T</sub> *1	V <sub>CE</sub> = 10V, I <sub>E</sub> = −5mA, f = 100MHz	-	250	-	MHz

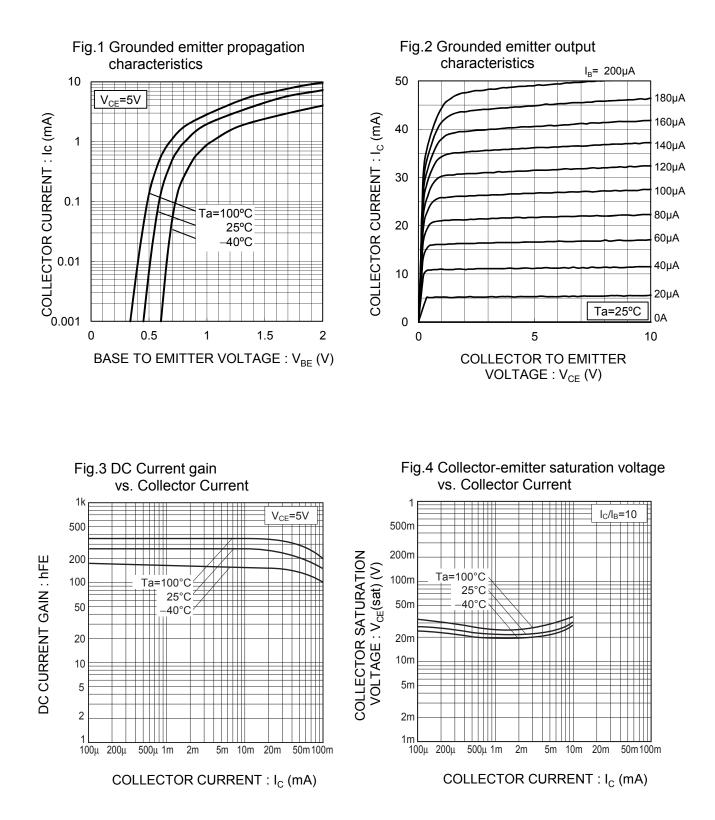
\*1 Characteristics of built-in transistor

\*2 Each terminal mounted on a reference footprint

\*3 120mW per element must not be exceeded.

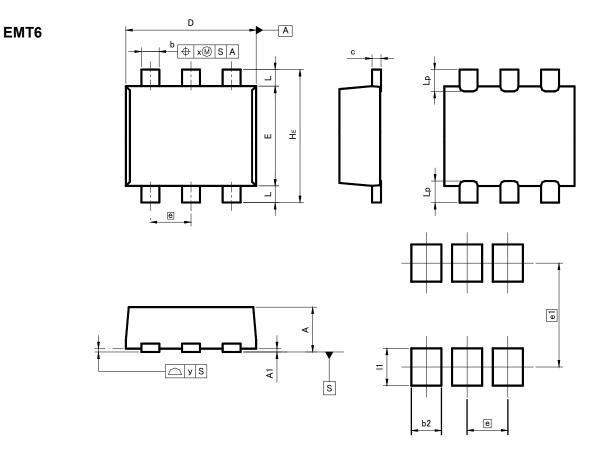
\*4 200mW per element must not be exceeded.

#### •Electrical characteristic curves(Ta = 25°C)



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#### •Dimensions (Unit : mm)



#### Patterm of terminal position areas

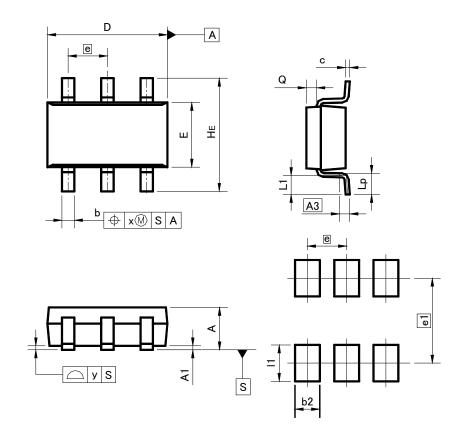
DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
A1	0.00	0.10	0	0.004	
Α	0.45	0.55	0.018	0.022	
b	0.17	0.27	0.007	0.011	
с	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
E	1.10	1.30	0.043	0.051	
е	0.	50	0.02		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	-	0.35	-	0.014	
x	_	0.10	_	0.004	
у	_	0.10	_	0.004	

DIM	DIM MILIMETERS MAX		INC	HES
DIN			MIN	MAX
e1	1.25		0.049	
b2	- 0.37		-	0.015
1	-	0.45	-	0.018

Dimension in mm/inches

#### •Dimensions (Unit : mm)

SMT6



#### Patterm of terminal position areas

DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
А	1.00	1.30	0.039	0.051
A1	0.00	0.10	0	0.004
A3	0.	25	0.	01
b	0.25	0.40	0.01	0.016
С	0.09	0.25	0.004	0.01
D	2.80	3.00	0.11	0.118
Е	1.50	1.80	0.059	0.071
е	0.	95	0.	04
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х	_	0.20	_	0.008
У	_	0.10	_	0.004

DIM	MILIMETERS		INC	HES
DIN	MIN MAX		MIN	MAX
e1	2.10		0.08	
b2	0.60		-	0.024
1	-	0.90	-	0.035

Dimension in mm/inches

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